



# Junction Capacitance

$w_D = f(V_r) = \sqrt{\frac{2\epsilon|V_r|}{qN_D}}$   
 $Q_{tot} = qN_D w_D$   
 $Q_{tot} = qN_D \sqrt{\frac{2\epsilon|V_r|}{qN_D}} = \sqrt{2\epsilon|V_r|qN_D}$   
 fixed capacitance:  $C = \frac{Q}{V}$   
 small-signal capacitance:  $C|_{V_r} = \frac{\partial Q}{\partial V}|_{V_r}$   
 $C|_{V_r} = \frac{\partial Q}{\partial V} = \frac{\partial}{\partial V} \sqrt{2\epsilon|V_r|qN_D} = \sqrt{2\epsilon q N_D} \frac{1}{2} |V_r|^{-1/2}, \quad V_r < 0$   
 $C|_{V_r} = \sqrt{\frac{\epsilon q N_D}{2|V_r|}} \quad \left(\frac{F}{cm^2}\right)$       "optimal doping"  
 $E_{max} = E_{crit} \rightarrow g_{ND} = \frac{\epsilon E_{crit}^2}{2V_{BV}}$

$$C|_{V_r} = \sqrt{\frac{\epsilon}{2|V_r|}} \sqrt{\frac{\epsilon E_{crit}^2}{2V_{BV}}} = \sqrt{\frac{\epsilon^2 E_{crit}^2}{4|V_r|V_{BV}}} \quad \text{valid for } |V_r| \gg \phi$$

In reality:  $V_{depl} = V_p - V_r$   
 if  $|V_r| \gg |V_p|$ ,  $V_{depl} \approx |V_r|$

More accurate:  
 $C|_{V_r} = \sqrt{\frac{\epsilon q N_D}{2(V_p - V_r)}}, \quad V_r < 0$

$$C_{j0} = C|_{\phi} = \sqrt{\frac{\epsilon q N_D}{2V_p}}$$

$$C_{jr} = C_{j0} \sqrt{\frac{V_p}{V_p - V_r}} = C_{j0} \sqrt{\frac{1}{1 - \frac{V_r}{V_p}}} \quad \left(\frac{F}{cm^2}\right)$$



# Schottky Capacitance Comparison

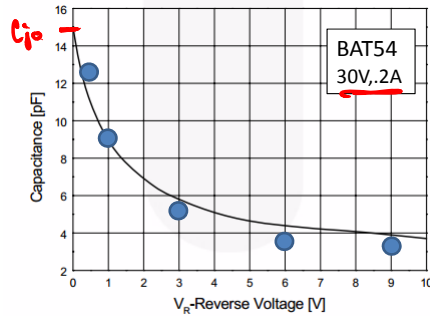
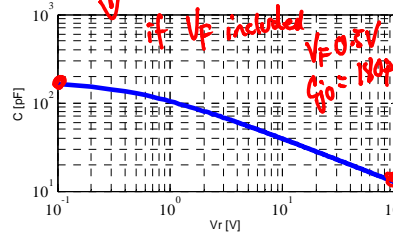
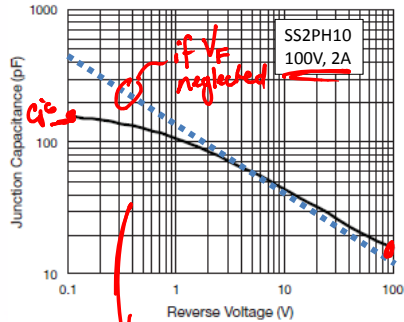
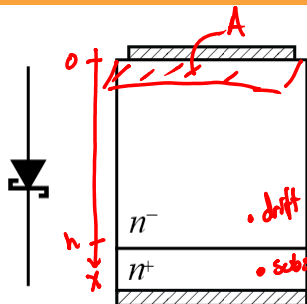


Figure 3. Total Capacitance vs. Reverse Voltage



# Drift Region Resistance



$$R = R_{\text{metals}} + R_{\text{contacts}} + R_{\text{subs}} + R_{\text{drift}}$$

$$R \approx R_{\text{drift}} \quad \text{valid for large } V_{\text{BV}}$$

$$\text{Resistivity: } \rho = \frac{1}{\mu_n n_0 q} \quad (\Omega \cdot \text{cm})$$

$$R = \rho \frac{h}{A} \rightarrow R_{\text{on,sp}} = \rho h = \rho h \quad (\Omega \cdot \text{cm}^2)$$

$$R_{\text{on,sp}} = \frac{1}{\mu_n n_0 q} h \rightarrow \text{select } h = W_D (E_{\text{max}} = E_{\text{crit}})$$

$$h = \sqrt{\frac{2 \epsilon V_{\text{BV}}}{q n_0}}$$

$$R_{\text{on,sp}} = \frac{1}{\mu_n n_0 q} \sqrt{\frac{2 \epsilon V_{\text{BV}}}{q n_0}} = \sqrt{\frac{2 \epsilon V_{\text{BV}}}{(q n_0)^3 \mu_n^2}} \quad (\Omega \cdot \text{cm}^2)$$



# Baliga's FOM

Baliga, B.J., "Advanced Power MOSFET Concepts"

$$g_{n,D} = \frac{\epsilon E_{crit}^2}{2V_{BV}}$$

$$R_{on,sp} = \sqrt{\frac{2\epsilon V_{BV}}{\mu_n^2}} \sqrt{\frac{1}{\left(\frac{\epsilon E_{crit}^2}{2V_{BV}}\right)^3}} = \sqrt{\frac{2^4 V_{BV}^4}{\mu_n^2 \epsilon^2 E_{crit}^6}} = \sqrt{\frac{4 V_{BV}^2}{\mu_n \epsilon E_{crit}^3}}$$

(max doping density to have  $E_{max} \leq E_{crit}$ )

Baliga's Figure of Merit